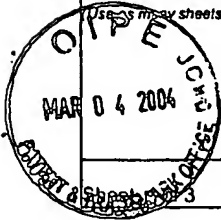


Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)



Complete If Known

Application Number	10/042,924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William
Attorney Docket No:	303.684US2

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-2002/0016081 A1	02/07/2002	Aloni, E. , et al.	438	714	10/15/2001
WV	US-3,387,286	06/04/1968	Dennard, Robert H.	340	173	07/14/1967
	US-4,173,766	11/06/1979	Hayes, James A.	357	23	09/16/1977
	US-4,409,723	10/18/1983	Harari, E.	29	571	09/08/1980
	US-4,435,785	03/06/1984	Chapman, Richard A.	365	147	06/02/1981
	US-5,020,030	05/28/1991	Huber, R. J.	365	185	10/31/1988
	US-5,596,214	01/21/1997	Endo, N.	257	324	05/01/1930
	US-5,740,104	04/14/1998	Forbes, Leonard	365	185.03	01/29/1997
	US-5,754,477	05/19/1998	Forbes, Leonard	365	185.33	01/29/1997
	US-5,768,193	06/16/1998	Lee, P. W., et al.	365	185.25	11/07/1996
	US-5,790,455	08/04/1998	Caywood, John M.	365	185.96	01/02/1997
	US-5,796,670	08/18/1998	Liu, Kwo-Jen	365	228	11/07/1996
	US-5,801,401	09/01/1998	Forbes, Leonard	257	77	01/29/1997
	US-5,852,306	12/22/1998	Forbes, Leonard	257	315	01/29/1997
	US-5,852,311	12/22/1998	Kwon, , et al.			06/05/1997
	US-5,886,368	03/23/1999	Forbes, Leonard , et al.	257	77	07/29/1997
	US-5,959,896	09/28/1999	Forbes, L.	365	185.33	02/27/1998
	US-5,989,958	11/23/1999	Forbes, Leonard	438	257	08/20/1998
	US-6,011,725	01/04/2000	Eitan, B.	365	185.33	02/04/1999
	US-6,025,627	02/15/2000	Forbes, Leonard , et al.	257	321	05/29/1998
	US-6,031,263	02/29/2000	Forbes, Leonard , et al.	257	315	07/29/1997
	US-6,063,668	05/16/2000	He, Y. , et al.	438	264	12/18/1997
	US-6,096,640	08/01/2000	Hu, Y.	438	652	04/02/1998
	US-6,100,559	08/08/2000	Park,	257	315	08/14/1998
	US-6,222,224	04/24/2001	Shigyo, N.	257	315	12/19/1997
	US-6,245,613	06/12/2001	Hsu, , et al.			04/24/2000
	US-6,246,089	06/12/2001	Lin, Yai-Fen , et al.	257	315	03/13/2000
	US-6,265,266	07/24/2001	Dejenfelt, A. T., et al.	438	258	09/27/1996
	US-6,351,428	02/26/2002	Forbes, Leonard	365	230.06	02/29/2000
WV	US-6,583,011	06/24/2003	Xia, L. , et al.	438	275	01/11/2000

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T?
---------------------	---------------------	------------------	-------------------------------------------------	-------	----------	----

EXAMINER

WV Vesperman

DATE CONSIDERED

3/21/04 , 4/15/04

Substitute Disclosure Statement Form (PTO-1449)

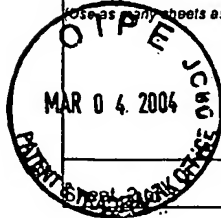
* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use as many sheets as necessary)



Complete if Known

Application Number	10/042,924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William

Attorney Docket No: 303.684US2

OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
WCU		CHAU, R., et al., "30nm Physical Gate Length CMOS Transistors with 1.0 ps n-MOS and 1.7 ps p-MOS Gate Delays", <u>IEEE Int. Electron. Devices Meeting, San Francisco, (December, 2000), pp. 45-48</u>	
		CHEN, IH-CHIN, et al., "A Physical Model for the Gate Current Injection in p-Channel MOSFET's", <u>IEEE Electron Device Letters, 14(5), (May 1993), 228-230</u>	
		CHEN, J., et al., "Hot Electron Gate Current and Degradation in P-Channel SOI MOSFET's", <u>1991 IEEE International SOI Conference Proceedings, Vail Valley, Colorado, (October 1991), pp. 8-9</u>	
		CHUNG, S. S., et al., "Performance and Reliability Evaluations of P-Channel Flash Memories with Different Programming Schemes", <u>International Electron Devices Meeting, Technical Digest, Washington, D.C., (December 1997), 295-298</u>	
		DIPERT, BRIAN, "Flash Memory Goes Mainstream", <u>IEEE Spectrum, 30(10), (October 1993), 48-52</u>	
		FRANK, J., et al., "Monte Carlo Simulations of p- and n-Channel Dual-Gate Si MOSFET's at the Limits of Scaling", <u>IEEE Transactions on Electron Devices, 40(11), (November 1993), pg. 2103</u>	
		GHODSI, RAMIN, et al., "Gate-Induced Drain-Leakage in Buried-Channel PMOS-A Limiting Factor in Development of Low-Cost, High-Performance 3.3-V, 0.25-um Technology", <u>IEEE Electron Device Letters, 19(9), (September 1998), 354-356</u>	
		HIRAYAMA, M., et al., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", <u>IEEE, (1999), 4 pages</u>	
		ILYAS, M., et al., "The optical absorption edge of amorphous thin films of silicon monoxide and of silicon monoxide mixed with titanium monoxide", <u>IEE, (2001), 1 page</u>	
		MULLER, D. A., "The Electronic Structure at the Atomic Scale of Ultrathin Gate Oxides", <u>Nature, 399, (June 1999), 758-761</u>	
		OHGURO, T., "Tenth Micron P-MOSFET's with Ultra-Thin Epitaxial Channel Layer Grown by Ultra-High-Vacuum CVD", <u>Proceedings: International Electron Devices Meeting, IEEE, Washington, Dec. 5-8, 1993, (Dec. 5, 1993), pp. 433-436</u>	
		OHNAKADO, T., et al., "1.5V Operation Sector-Erasable Flash Memory with Bipolar Transistor Selected (BITS) P-Channel Cells", <u>1998 Symposium on VLSI Technology, Digest of Technical Papers, (1998), 14-15</u>	
		OHNAKADO, T., et al., "Novel Electron Injection Method Using Band-to-Band Tunneling Induced Hot Electron (BBHE) for Flash Memory with a P-Channel Cell", <u>1995 International Electron Devices Meeting TECHNICAL DIGEST, Washington D.C., (1995), pp. 279-282</u>	
WCU		OHNAKADO, T., et al., "Novel Self-Limiting Program Scheme Utilizing N-Channel Select Transistors in P-Channel DINOR Flash Memory", <u>1996 International Electron Devices Meeting TECHNICAL DIGEST, San Francisco,</u>	

EXAMINER

DATE CONSIDERED

3/24/04, 4/15/04

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached

BEST AVAILABLE COPY

PTO/SB/06A(10-01)
Approved for use through 10/31/2002. OMB 851-0001
US Patent & Trademark Office U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/042,924
	Filing Date	January 9, 2002
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2813
	Examiner Name	Vesperman, William
		Attorney Docket No: 303.684US2

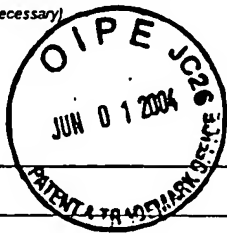
OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		CA, (1996), pp. 181-184	
WAV		PAPADAS, C. , "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", <u>IEEE Transaction on Electron Devices</u> , 42, (April 1995), 678-682	
		PATEL, N. K., et al., "Stress-Induced Leakage Current in Ultrathin SiO2 Films", <u>Appl. Phys. Letters</u> , 64(14), (April 1994), 1809-1811	
		SALM, C. , et al., "Gate Current and Oxide Reliability in p+ Poly MOS Capacitors with Poly-Si and Poly-Ge0.3Si0.7 Gate Material", <u>IEEE Electron Device Letters</u> 19(7), (July 1998), 213-215	
		SHI, YING , et al., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", <u>IEEE Electron Device Letters</u> , 19(10), (October 1998), 388-390	
		STRASS, A. , et al., "Fabrication and Characterisation of thin low-temperature MBE-compatible silicon oxides of different stoichiometry", <u>Thin Solid Films</u> 349, (1999), pp. 135-146	
		TIWARI, SANDIP , "Volatile and Non-Volatile Memories in Silicon with Nano-Crystal Storage", <u>Int'l Electron Devices Meeting: Technical Digest</u> , Washington, DC, (Dec. 1995), 521-524	
WAV		WU, Y. , et al., "Time Dependent Dielectric Wearout (TDDW) Technique for Reliability of Ultrathin Gate Oxides", <u>IEEE Electron Device Letters</u> , 20(6), (June 1999), 262-264	

EXAMINER	William Vesperman	DATE CONSIDERED	3/28/04, 4/15/04
----------	-------------------	-----------------	------------------

Substitute Disclosure Statement Form (PTO-1449)
* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

TEST AVAILABLE COPY

Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
 (Use as many sheets as necessary)



Sheet 1 of 1

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

PTO/SB/004(10-01)
 Approved for use through 10/31/2002, OMB 651-0001
 US Patent & Trademark Office U.S. DEPARTMENT OF COMMERCE

Complete if Known

Application Number	10/042924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William

Attorney Docket No: 303.684US2

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
WV	US-6,297,103	10/02/2001	Ahn, Kie, et al.	438	275	02/28/2000
WV	US-6,456,535	09/24/2002	Forbes, L., et al.	365	185.28	06/15/2001
WV	US-6,605,961	08/12/2003	Forbes, L.	326	41	02/29/2000
WV	US-6,639,835	10/28/2003	Forbes, L.	365	186.14	02/29/2000
WV	US-6,720,221	04/13/2004	Ahn, Kie, et al.	438	275	08/30/2001
WV	US-6,730,960	05/04/2004	Forbes, L.	257	321	08/30/2001

EXAMINER

WV Vesperman

DATE CONSIDERED

10/21/04

Substitute Disclosure Statement Form (PTO-1449)
 * EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached